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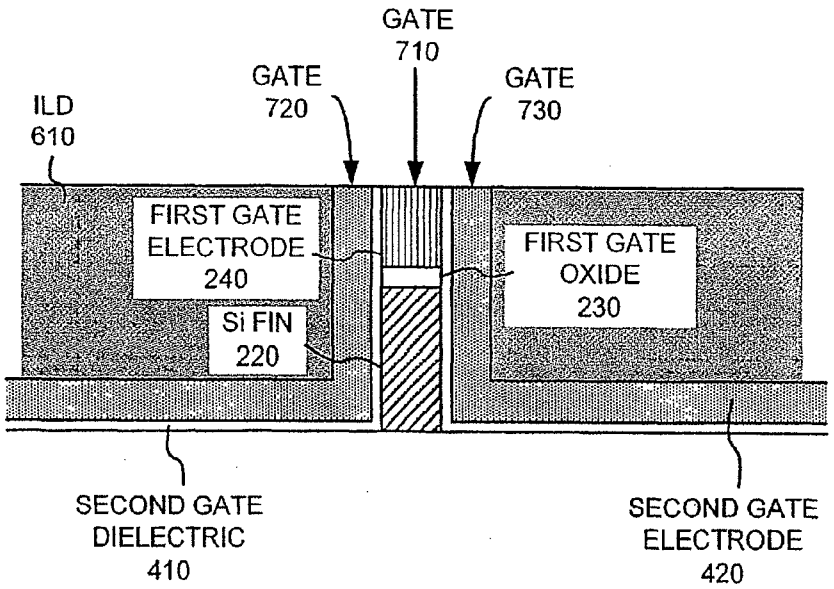
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(54) **Title:** DOUBLE AND TRIPLE GATE MOSFET DEVICES AND METHODS FOR MAKING SAME




(57) **Abstract:** A double gate metal-oxide semiconductor field-effect transistor (MOSFET) includes a fin (220), a first gate (240) and a second gate (420). The first gate (240) is formed on top of the fin (220). The second gate (420) surrounds the fin (220) and the first gate (240). In another implementation, a triple gate MOSFET includes a fin (220), a first gate (710), a second gate (720), and a third gate (730). The first gate (710) is formed on top of the fin (220). The second gate (720) is formed adjacent the fin (220). The third gate (730) is formed adjacent the fin (220) and opposite the second gate (720).

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